SAMYANG ELECTRONICS

TB2S---TB10S

SILICON BRIDGE RECTIFIERS

Reverse Voltage: 200 - 1000V
Forward Current: 0.8,1.0A

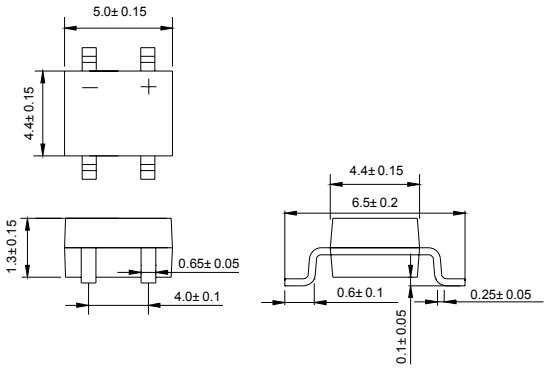
FEATURES

- Glass passivated chip junction
- Plastic materrial has U/L flammability classification 94v-O
- High surge overload rating: 30A peak
- Save space on printed circuit boards
- High temperature soldering guaranteed:
  260°C/10 seconds at 5 lbs. (2.3 kg) tension

MECHANICAL DATA

- **Case:** Molded plastic body over passivated junctions
- **Terminals:** Plated leads solderable per MIL-STD-750, Method 2026
- **Polarity:** Polarity symbols marked on body
  Dimensions in inches and (millimeters)
- **Mounting Position:** Any
- **Weight:** 0.003 ounces, 0.090g

TBS



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate by 20%.

Parameter	Symbol	TB2S	TB4S	TB6S	TB8S	TB10S	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	200	400	600	800	1000	V
Maximum RMS voltage	V_{RWS}	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	200	400	600	800	1000	V
Maximum average forward output current T_L=100°C	$I_{F(AV)}$	0.8[1)] 1.0[2)]					A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load	I_{FSM}	30					A
Maximum instantaneous forward voltage at 0.4A	V_F	0.95					V
Maximum reverse current @T_A=25°C at rated DC blocking voltage	I_R	10					uA
Typical thermal resistance junction to lead On aluminum substrate On glass-epoxy substrate	R_{JL} R_{JA}	25 62.5 80					°C/W
Operating junction temperature range	T_J	-55---+150					°C
Storage temperature range	T_{STG}	-55---+150					°C

NOTES: 1). On glass epoxy P.C.B.
2). On aluminum substrate

FIG.1 TYPICAL FORWARD CHARACTERISTICS

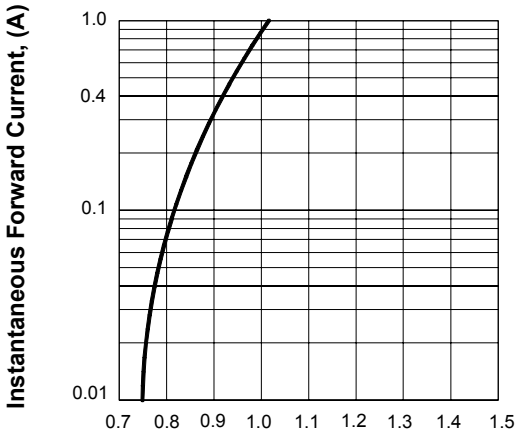


FIG.2 FORWARD DERATING CURVE

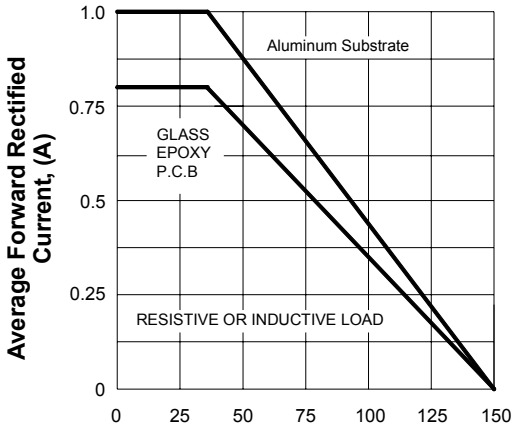


FIG.3 TYPICAL REVERSE CHARACTERISTICS

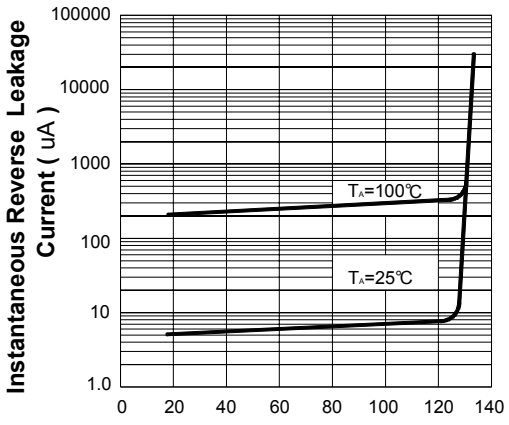


FIG.4 PEAK FORWARD SURGE CURRENT

